

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a semiconductor laser device, comprising the steps of: forming an electrode pattern on an upper surface of a semiconductor wafer stacked at least
5 a light emission layer; cutting the resultant semiconductor wafer for predetermined width to yield a plurality of semiconductor bars; and sectioning the semiconductor bars into a desired size to form semiconductor laser devices having a pair of cleavage surfaces which are parallel to a chip-width
10 direction and distant from each other by a predetermined resonator length, wherein the electrode pattern formed in the step of forming an electrode pattern is continuous at least in a resonator-length direction.